ELECTRONIC INFORMATION DISCLOSURE STATEMENT

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> Title of Invention

METHOD FOR FABRICATING A NITRIDED SILICON-OXIDE GATE DIELECTRIC

Application Number:

Confirmation Number:

First Named Applicant: Jay Burnham

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Art Unit: Examiner:

Search string: (6399445 or 6380056 or 6368923 or 6335252 or 6291867 or 6200651 or 6114258

or 6136654 or 6171911 or 6027977 or 5726087 or 5648284 or 5596218 or 5445999

or 5219773 or 4621277).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	6399445	2002-06-04	Hattangady et al			
	2	6380056	2002-04-30	Shue et al			
	3	6368923	2002-04-09	Huang			
	4	6335252	2002-01-01	Oishi et al			
	5	6291867	2001-09-18	Wallace et al			
	6	6200651	2001-03-13	Roche et al			
	7	6114258	2000-09-05	Miner et al			
	8	6136654	2000-10-24	Kraft et al			
	9	6171911	2001-01-09	Yu			
	10	6027977	2000-02-22	Mogami			
	11	5726087	1998-03-10	Tseng et al			
	12	5648284	1997-07-15	Kusunoki et al			
	13	5596218	1997-01-21	Soleimani et al			
	14	5445999	1995-08-29	Thakur et al			
	15	5219773	1993-06-15	Dunn			
	16	4621277	1986-11-04	Ito et al			

Signature

Examiner Name	Date